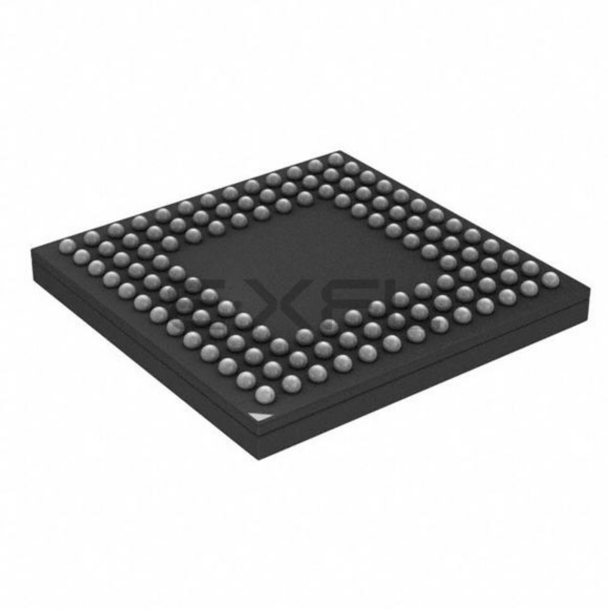
Silicon Labs - EFM32GG895F1024G-E-BGA120 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	93
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg895f1024g-e-bga120

2.1.11 TFT Direct Drive

The EBI contains a TFT controller which can drive a TFT via a 565 RGB interface. The TFT controller supports programmable display and port sizes and offers accurate control of frequency and setup and hold timing. Direct Drive is supported for TFT displays which do not have their own frame buffer. In that case TFT Direct Drive can transfer data from either on-chip memory or from an external memory device to the TFT at low CPU load. Automatic alpha-blending and masking is also supported for transfers through the EBI interface.

2.1.12 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C-bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I^2C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

2.1.13 Universal Synchronous/Asynchronous Receiver/Transmitter (USART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, IrDA and I2S devices.

2.1.14 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Autobaud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.15 Universal Asynchronous Receiver/Transmitter (UART)

The Universal Asynchronous serial Receiver and Transmitter (UART) is a very flexible serial I/O module. It supports full- and half-duplex asynchronous UART communication.

2.1.16 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique $\text{LEUART}^{\text{TM}}$, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.17 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output. TIMER0 also includes a Dead-Time Insertion module suitable for motor control applications.

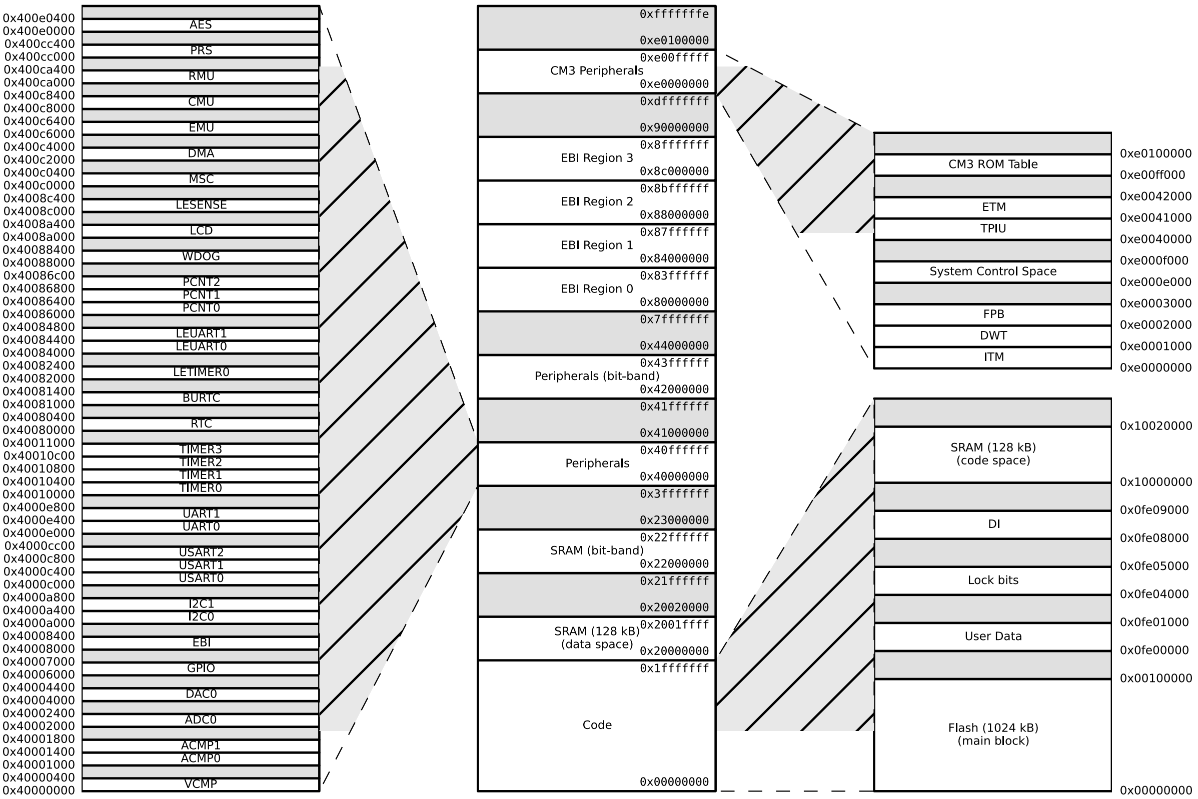
2.1.18 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.3 Memory Map

The *EFM32GG895* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32GG895 Memory Map with largest RAM and Flash sizes



3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from flash. (Production test condition = 14MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		219	240	µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		205	225	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		206	229	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		209	232	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		211	234	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		215	242	µA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		243	327	µA/ MHz
I_{EM1}	EM1 current (Production test condition = 14MHz)	48 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		80	90	µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		80	90	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		81	91	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		83	99	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		85	100	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		90	102	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V		122	152	µA/ MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		1.1[1]	1.9[1]	µA
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		8.8[1]	21.5[1]	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.8[1]	1.5[1]	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		8.2[1]	20.3[1]	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.08	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.5	2.5	µA

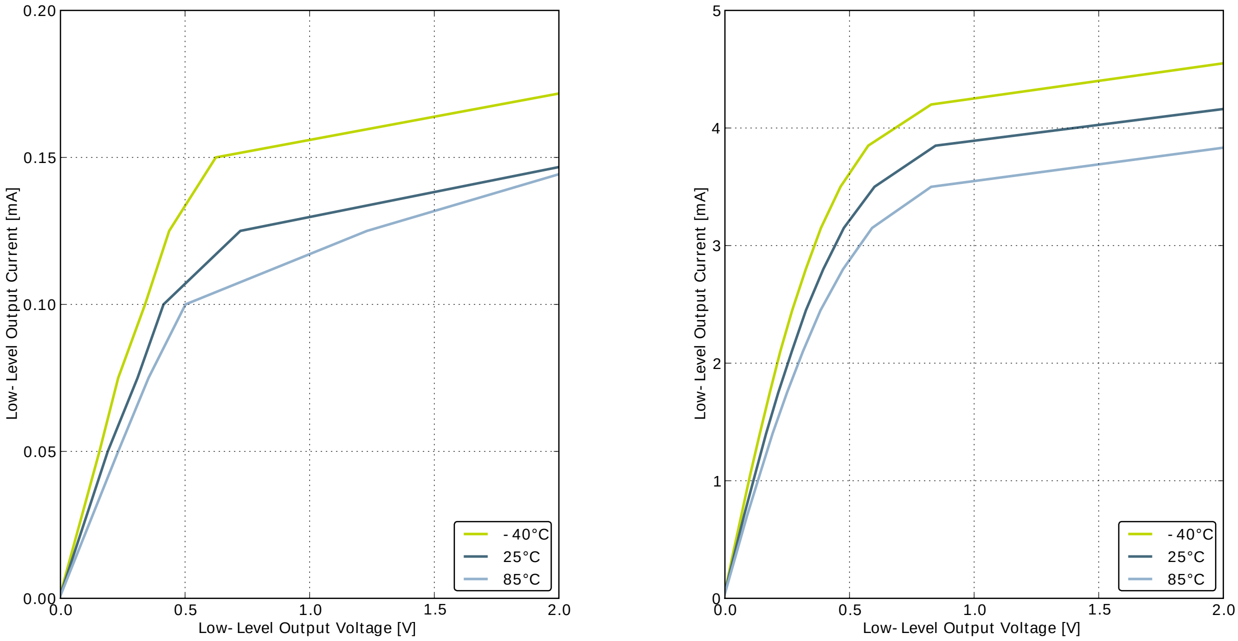
[1] Only one RAM block enabled. The RAM block size is 32 kB.

3.8 General Purpose Input Output

Table 3.7. GPIO

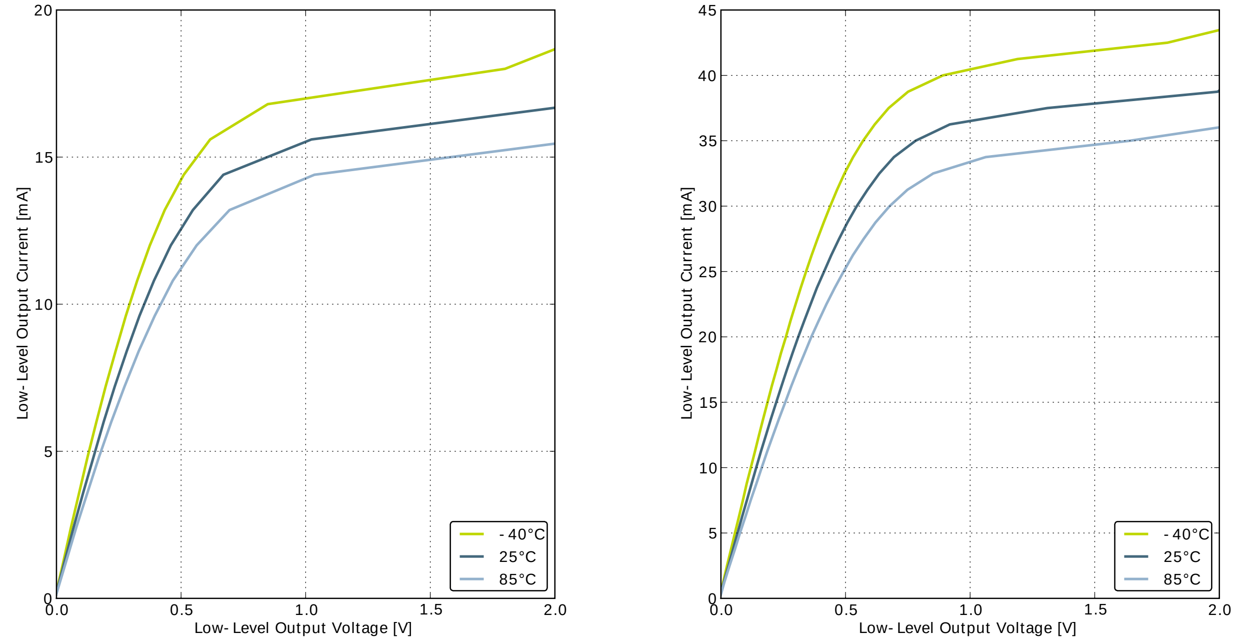
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$	V
V_{IOIH}	Input high voltage		$0.70V_{DD}$			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V

Figure 3.4. Typical Low-Level Output Current, 2V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

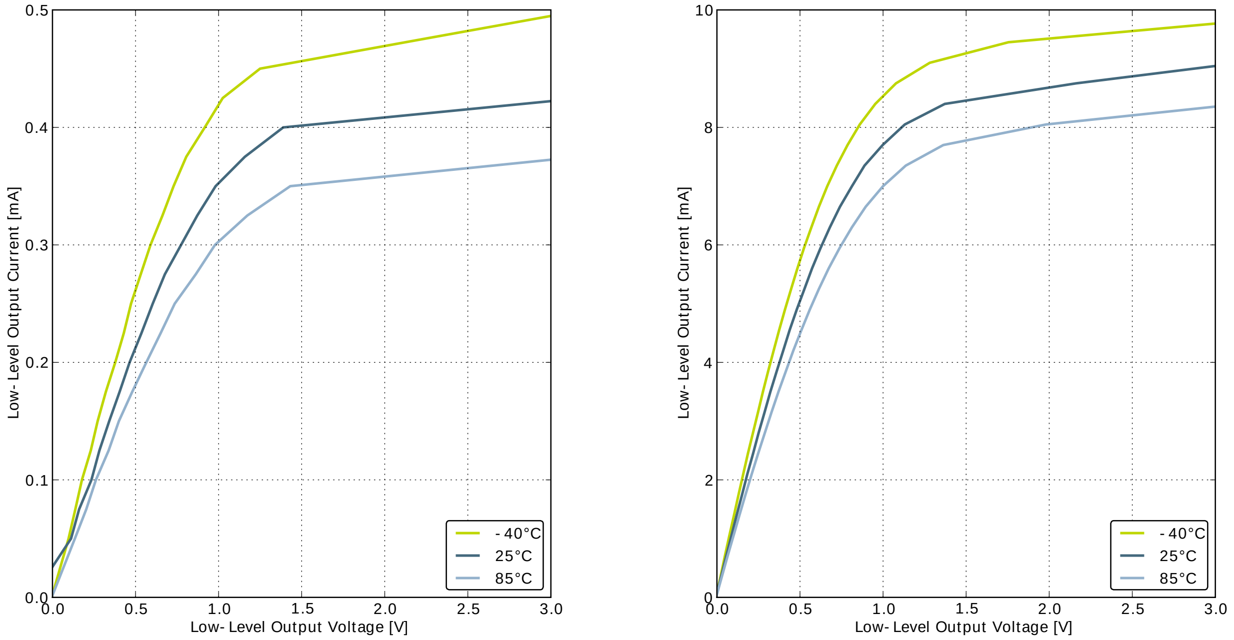
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

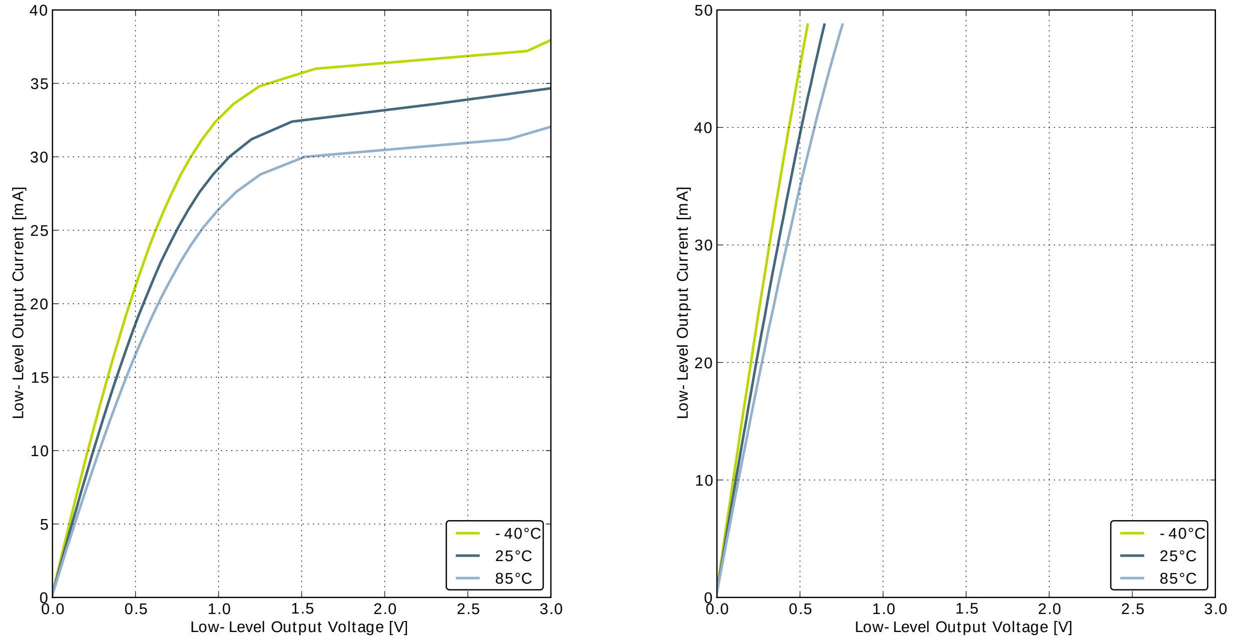
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

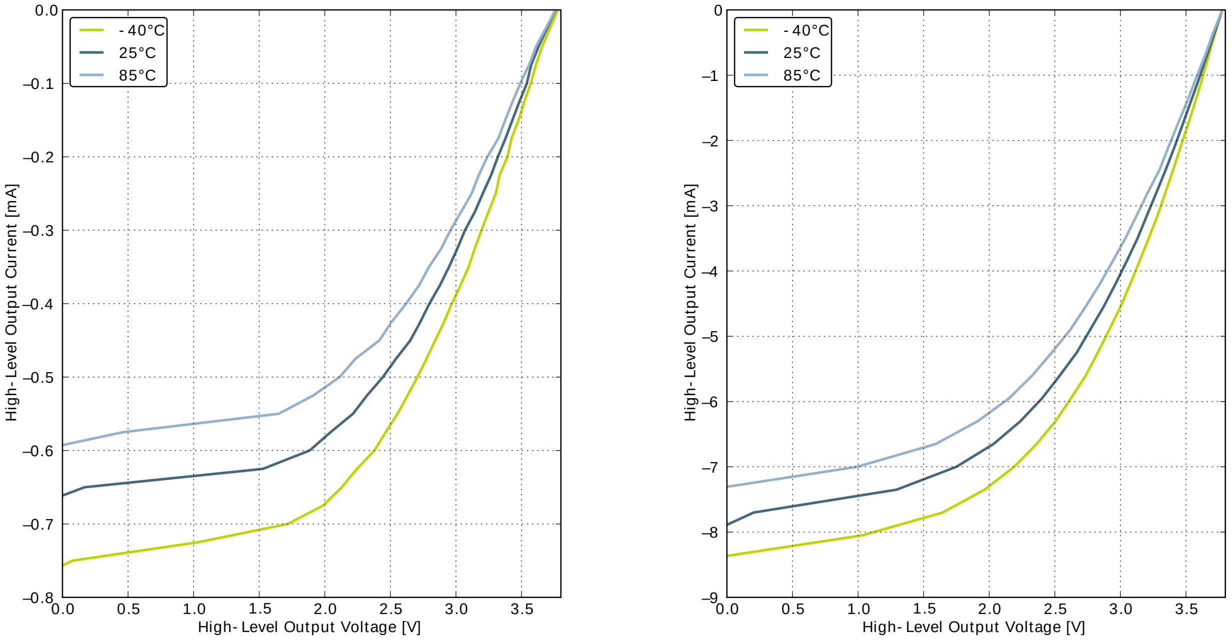
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

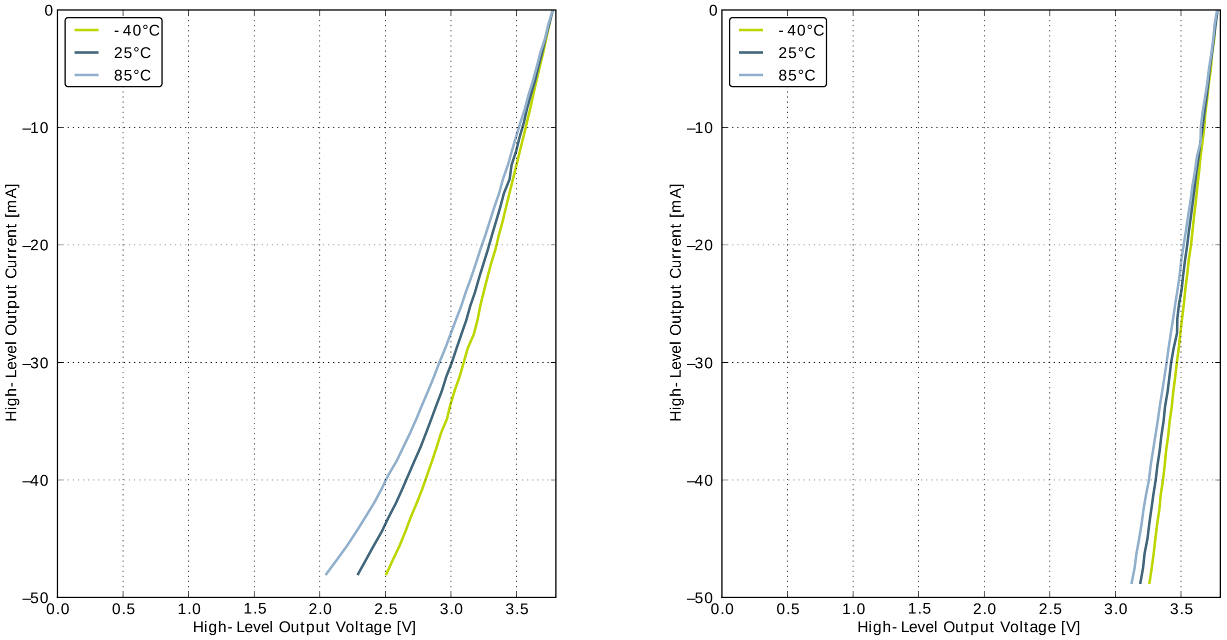
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.9. Typical High-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{ADCIN}	Input capacitance			2		pF
R_{ADCIN}	Input ON resistance		1			MOhm
$R_{ADCFILT}$	Input RC filter resistance			10		kOhm
$C_{ADCFILT}$	Input RC filter/decoupling capacitance			250		fF
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		µs
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$GAIN_{ED}$	Gain error drift	1.25V reference		0.01[2]	0.033[3]	%/°C
		2.5V reference		0.01[2]	0.03[3]	%/°C
$OFFSET_{ED}$	Offset error drift	1.25V reference		0.2[2]	0.7[3]	LSB/°C
		2.5V reference		0.2[2]	0.62[3]	LSB/°C

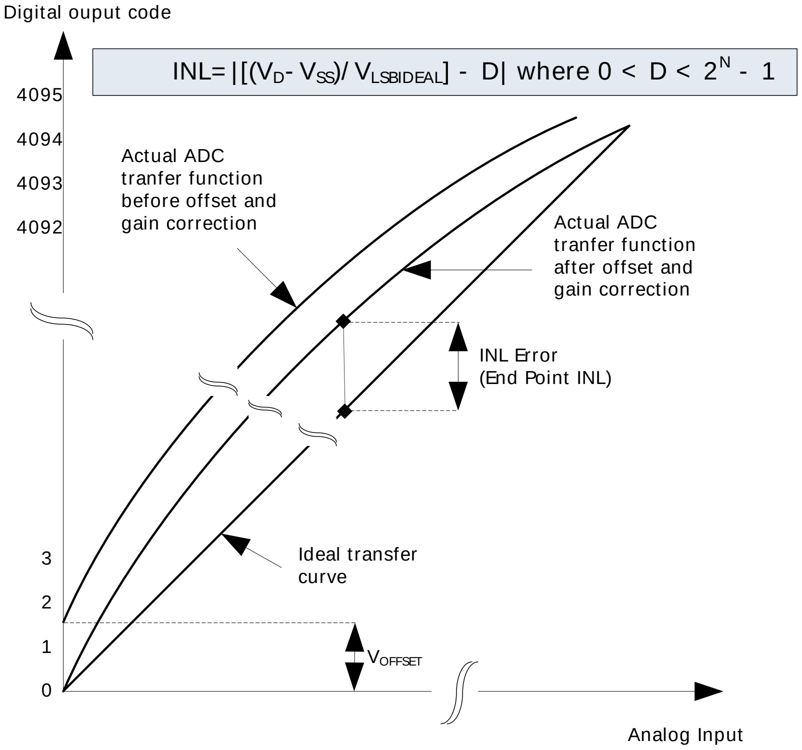
[1] On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

[2] Typical numbers given by abs(Mean) / (85 - 25).

[3] Max number given by (abs(Mean) + 3x stddev) / (85 - 25).

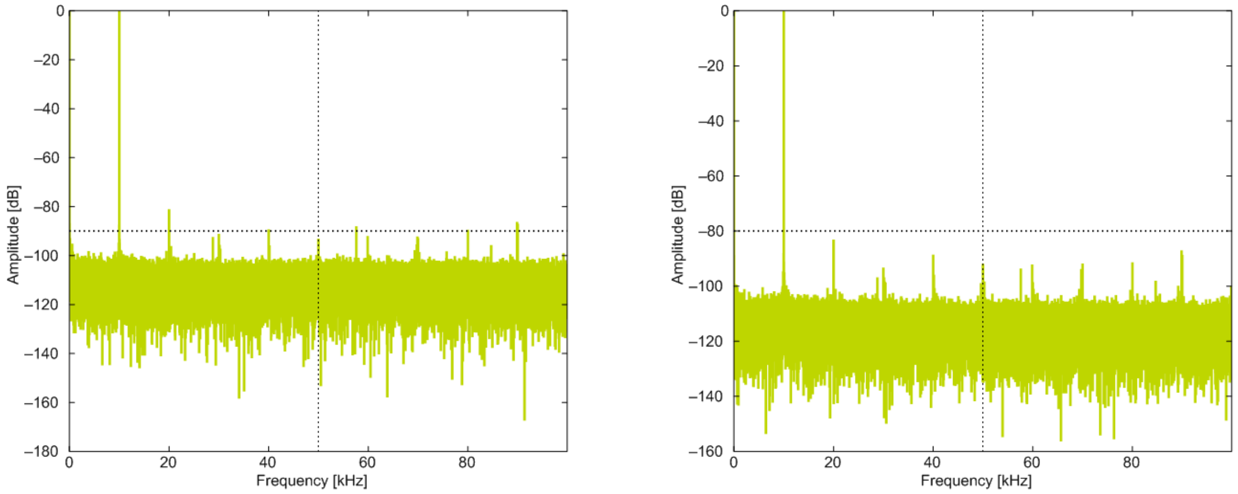
The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.17 (p. 32) and Figure 3.18 (p. 33) , respectively.

Figure 3.17. Integral Non-Linearity (INL)



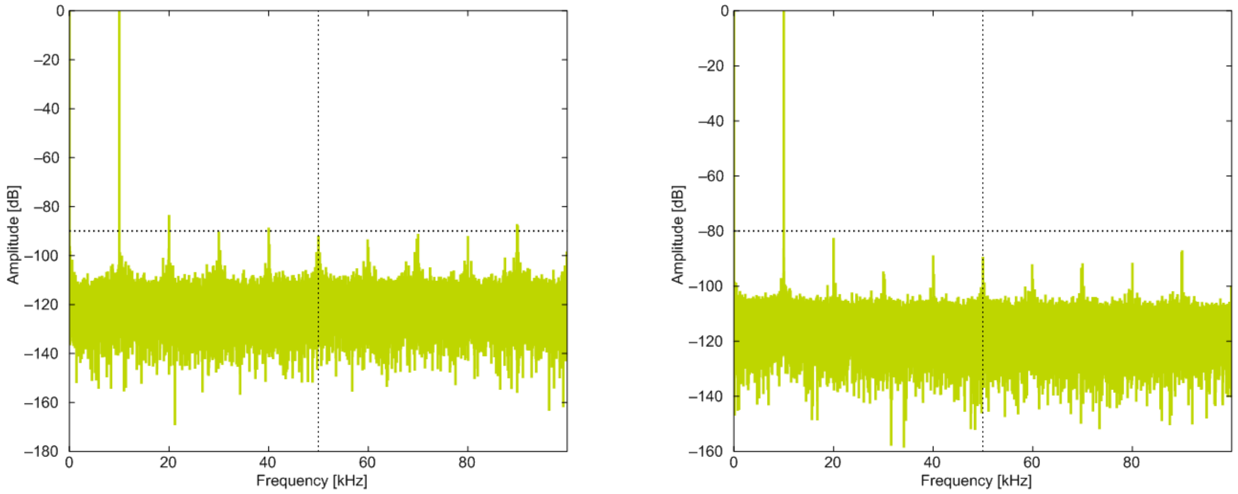
3.10.1 Typical performance

Figure 3.19. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



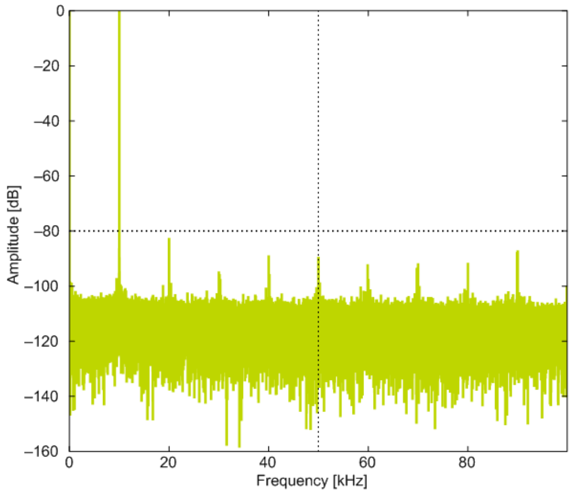
1.25V Reference

2.5V Reference



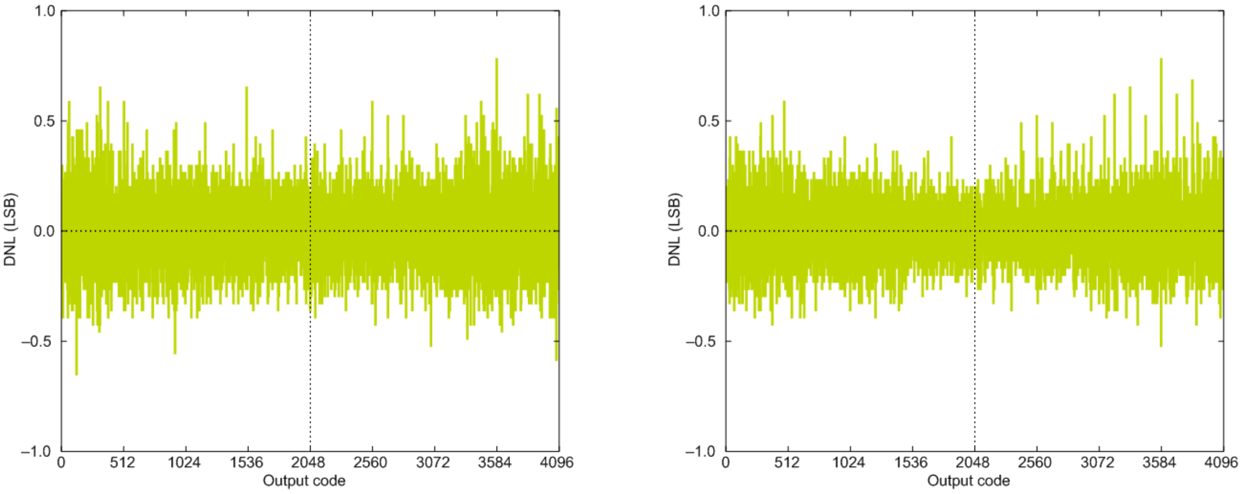
2XVDDVSS Reference

5VDIFF Reference



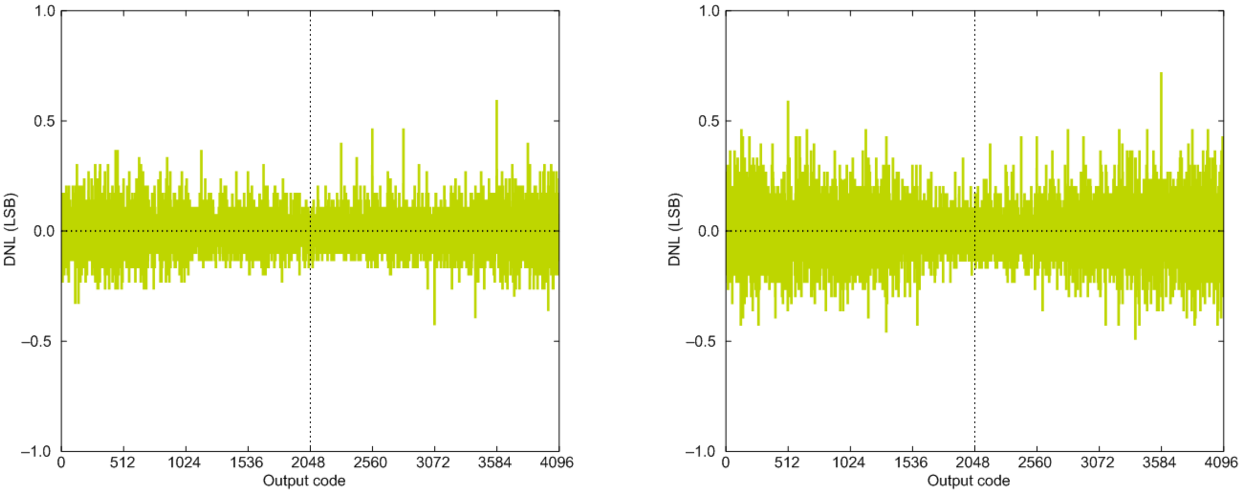
VDD Reference

Figure 3.21. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C



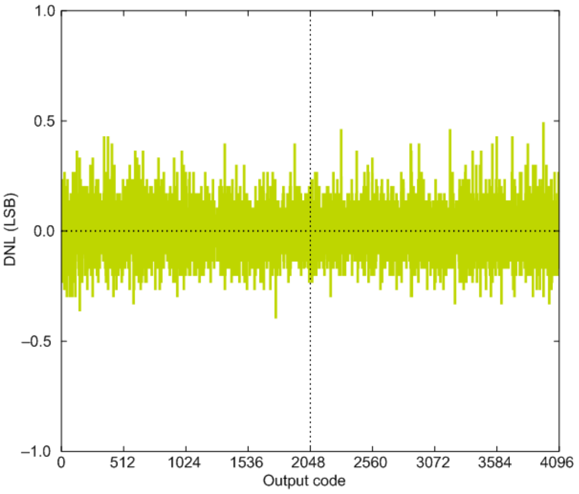
1.25V Reference

2.5V Reference



2XVDDVSS Reference

5VDIFF Reference



VDD Reference

Figure 3.27. OPAMP Negative Power Supply Rejection Ratio

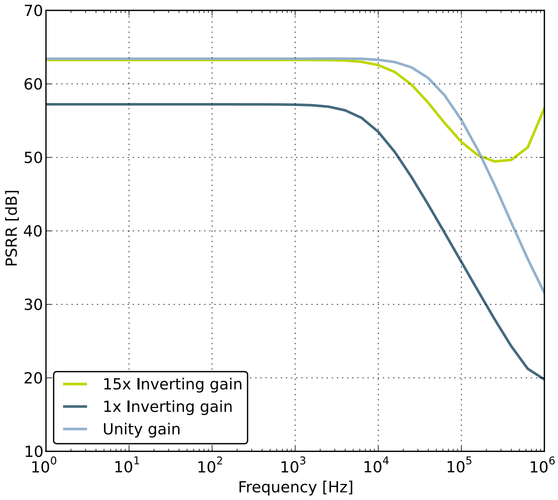


Figure 3.28. OPAMP Voltage Noise Spectral Density (Unity Gain) V_{out}=1V

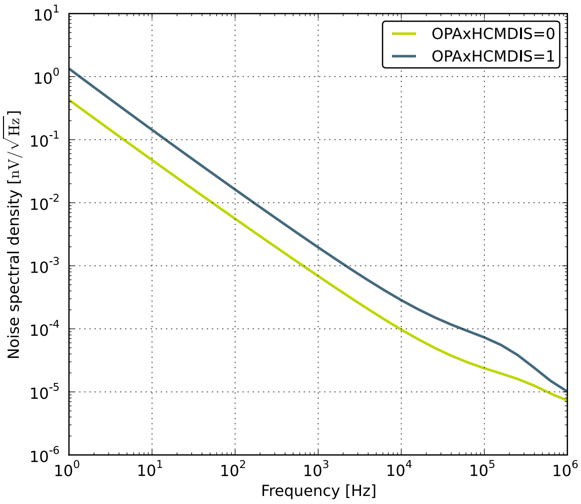
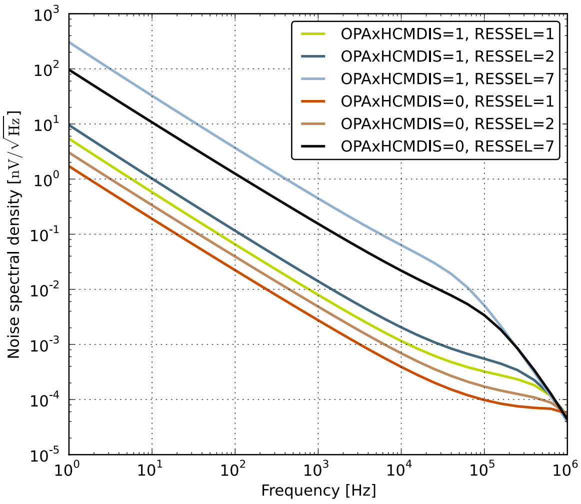


Figure 3.29. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)



3.14 Voltage Comparator (VCMP)

Table 3.18. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{VCMPIN}	Input voltage range			V_{DD}		V
V_{VCMPCM}	VCMP Common Mode voltage range			V_{DD}		V
I_{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	µA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	µA
$t_{VCMPREF}$	Startup time reference generator	NORMAL		10		µs
$V_{VCMPOFFSET}$	Offset voltage	Single ended	-230	-40	190	mV
		Differential		10		mV
$V_{VCMPHYST}$	VCMP hysteresis			40		mV
$t_{VCMPSTART}$	Startup time				10	µs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD\ Trigger\ Level}=1.667V+0.034\times TRIGLEVEL \tag{3.2}$$

3.15 EBI

Figure 3.31. EBI Write Enable Timing

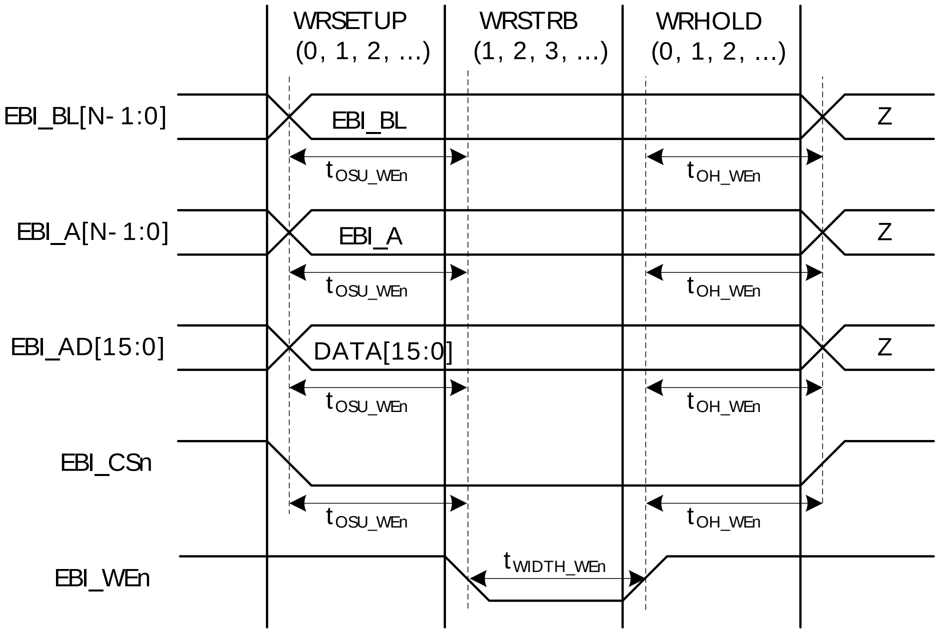


Table 3.19. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_WEn} [1,2,3,4]	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	-6.00 + (WRHOLD * $t_{HFCORECLK}$)			ns
t_{OSU_WEn} [1,2,3,4,5]	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	-14.00 + (WRSETUP * $t_{HFCORECLK}$)			ns
t_{WIDTH_WEn} [1,2,3,4,5]	EBI_WEn/EBI_NANDWEn pulse width	-7.00 + ((WRSTRB +1) * $t_{HFCORECLK}$)			ns

[1] Applies for all addressing modes (figure only shows D16 addressing mode)

[2] Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)

[3] Applies for all polarities (figure only shows active low signals)

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by 1/2 * $t_{HFCLKNODIV}$.

Figure 3.32. EBI Address Latch Enable Related Output Timing

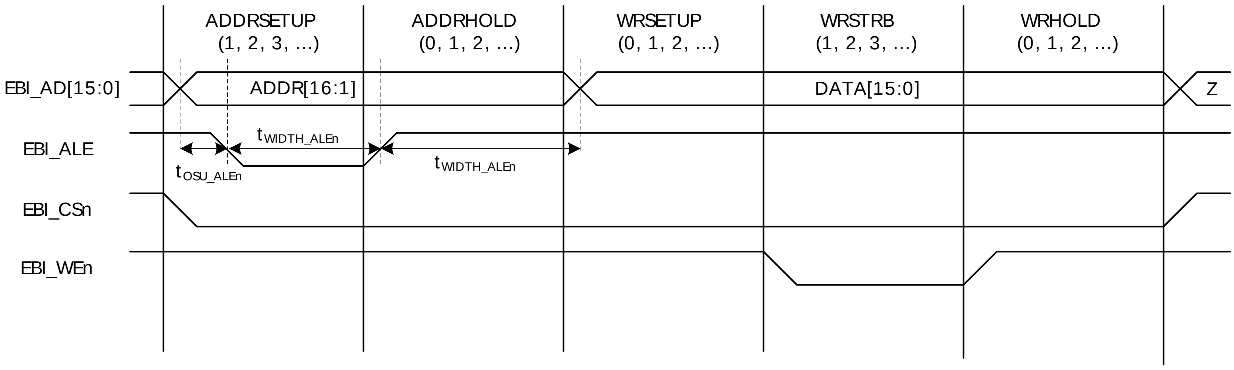


Table 3.20. EBI Address Latch Enable Related Output Timing

Symbol	Parameter	Min	Typ	Max	Unit
t_{OH_ALEn} [1,2,3,4]	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	-6.00 + (ADDRHOLD[5] * $t_{HFCORECLK}$)			ns
t_{OSU_ALEn} [1,2,4]	Output setup time, from EBI_AD valid to leading EBI_ALE edge	-13.00 + (0 * $t_{HFCORECLK}$)			ns
t_{WIDTH_ALEn} [1,2,3,4]	EBI_ALEn pulse width	-7.00 + (ADDRSETUP+1) * $t_{HFCORECLK}$)			ns

[1] Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)

[2] Applies for all polarities (figure only shows active low signals)

[3] The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of tOH_ALEn by $t_{HFCORECLK}$ - 1/2 * $t_{HFCLKNODIV}$.

[4] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of $_{VDD}$)

[5] Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Table 3.27. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and START condition	0.5			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32GG Reference Manual.

3.18 USART SPI

Figure 3.36. SPI Master Timing

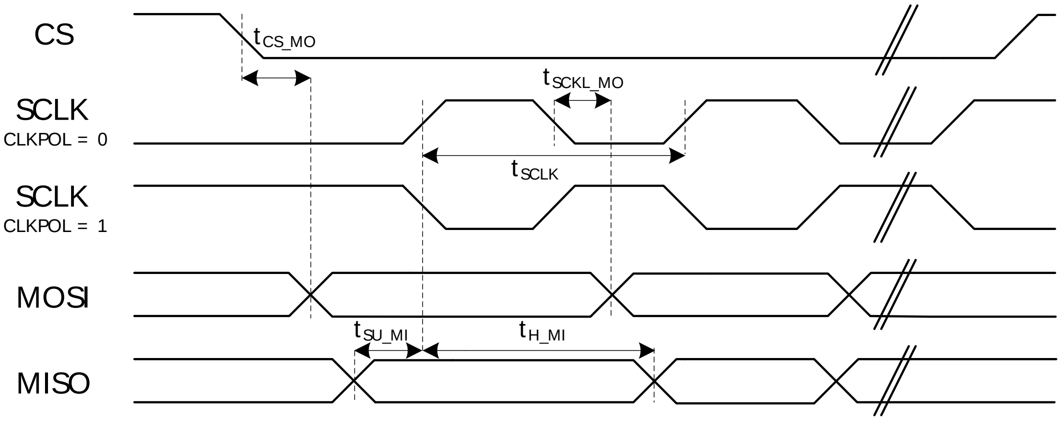


Table 3.28. SPI Master Timing

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{SCLK} [1,2]	SCLK period		$2 * t_{HFPERCLK}$			ns
t_{CS_MO} [1,2]	CS to MOSI		-2.00		1.00	ns
t_{SCLK_MO} [1,2]	SCLK to MOSI		-4.00		3.00	ns
t_{SU_MI} [1,2]	MISO setup time	IOVDD = 1.98 V	36.00			ns
		IOVDD = 3.0 V	29.00			ns
t_{H_MI} [1,2]	MISO hold time		-4.00			ns

[1] Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

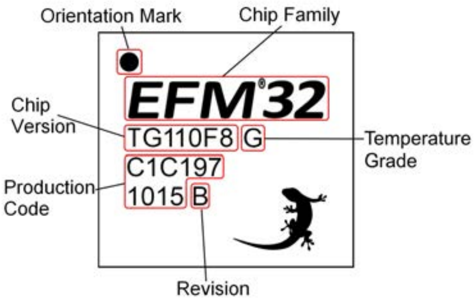
[2] Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 72) .

6.3 Errata

Please see the errata document for EFM32GG895 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:
http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.40

March 21st, 2016

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Reduced maximum and typical current consumption for all EM0 entries except 48 MHz in the Current Consumption table in the Electrical Characteristics section.

Increased maximum specifications for EM2 current, EM3 current, and EM4 current in the Current Consumption table in the Electrical Characteristics section.

Increased typical specification for EM2 and EM3 current at 85 C in the Current Consumption table in the Electrical Characteristics section.

Added EM2, EM3, and EM4 current consumption vs. temperature graphs.

Added a new EM2 entry and specified the existing specification is for EM0 for the BOD threshold on falling external supply voltage in the Power Management table in the Electrical Characteristics section.

Reduced maximum input leakage current in the GPIO table in the Electrical Characteristics section.

Added a maximum current consumption specification to the LFRCO table in the Electrical Characteristics section.

Added maximum specifications for the active current including references for two channels to the DAC table in the Electrical Characteristics section.

Increased the maximum specification for DAC offset voltage in the DAC table in the Electrical Characteristics section.

Increased the typical specifications for active current with FULLBIAS=1 and capacitive sense internal resistance in the ACMP table in the Electrical Characteristics section.

Added minimum and maximum specifications and updated the typical value for the VCMP offset voltage in the VCMP table in the Electrical Characteristics section.

Removed the maximum specification and reduced the typical value for hysteresis in the VCMP table in the Electrical Characteristics section.

Updated all graphs in the Electrical Characteristics section to display data for 2.0 V as the minimum voltage.

7.2 Revision 1.30

May 23rd, 2014

Removed "preliminary" markings

Updated HFRCO figures.

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated Current Consumption information.

Updated Power Management information.

Updated PCB Land Pattern, PCB Solder Mask and PCB Stencil Design figures.

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.98

May 25th, 2012

Corrected BGA solder balls material description.

Corrected EM3 current consumption in the Electrical Characteristics section.

7.8 Revision 0.96

February 28th, 2012

Added reference to errata document.

Corrected BGA120 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.9 Revision 0.95

September 28th, 2011

Flash configuration for Giant Gecko is now 1024KB or 512KB. For flash sizes below 512KB, see the Leopard Gecko Family.

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level to Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added Opamp pinout overview.

Added reference to errata document.

Corrected BGA120 package drawing.

Updated PCB land pattern, solder mask and stencil design.

Table of Contents

List of Tables